Next Generation HV-MAPS for Future Detectors at Large Accelerator Facilities

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VertexPix

A HV-MAPS sensor in IHP130nm, utilizing SiGe-Bipolar transistors

- Continuation of 21-24 effort
- Finish characterisation of existing small scale prototypes
- Investigation of radiation tolerance
- ⇒Development of the first fully monolithic small scale sensor





Internal Gain Layer for HV-MAPS

Utilizing epitaxial wafers with a buried gain layer to further enhance HV-MAPS performance

- Feasibility proven in IHP130nm (L.Paolozzi)
- TCAD study to find suitable epitaxial structures
- Produce a known sensor on the new wafers
- Investigate its performance gain



